# 2SC3513

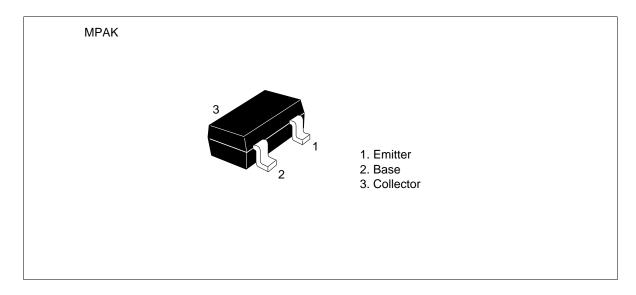
# Silicon NPN Epitaxial

# **HITACHI**

## **Application**

UHF / VHF wide band amplifier

#### Outline





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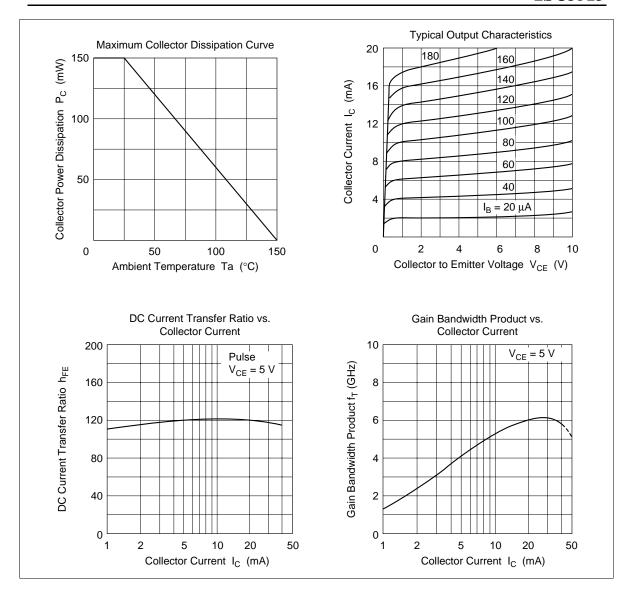
# Absolute Maximum Ratings ( $Ta = 25^{\circ}C$ )

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	15	V
Collector to emitter voltage	V <sub>CEO</sub>	11	V
Emitter to base voltage	$V_{EBO}$	2	V
Collector current	I <sub>c</sub>	50	mA
Collector power dissipation	P <sub>c</sub>	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

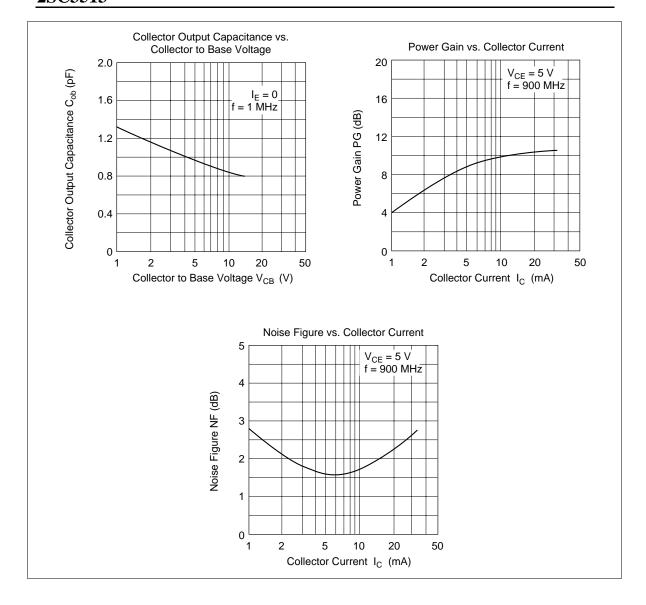
### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	15	_	_	V	$I_{C} = 10 \ \mu A, \ I_{E} = 0$
Collector cutoff current	I <sub>CEO</sub>	_	_	1	μΑ	V <sub>CE</sub> = 10 V, R <sub>BE</sub> = ∞
Emitter cutoff current	I <sub>EBO</sub>	_	_	1	μΑ	$V_{EB} = 1 \text{ V}, I_{C} = 0$
Collector cutoff current	$I_{\text{CBO}}$	_		1	μΑ	$V_{CB} = 12 \text{ V}, I_{E} = 0$
DC current transfer ratio	$h_{FE}$	50	120	250		$V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA}$
Collector output capacitance	Cob	_	1.0	1.5	pF	$V_{CB} = 5 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$
Gain bandwidth product	$f_{T}$	_	6.0	_	GHz	$V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA}$
Power gain	PG	_	10	_	dB	$V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA},$ f = 900 MHz
Noise figure	NF	_	1.6	_	dB	$V_{CE} = 5 \text{ V}, I_{C} = 5 \text{ mA},$ f = 900 MHz

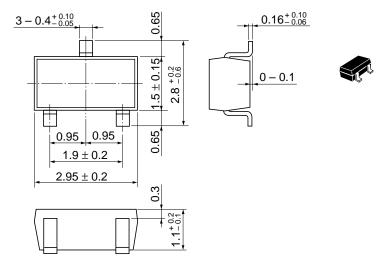
Note: Marking is "IS-".



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#### Unit: mm



Hitachi Code	MPAK
JEDEC	_
EIAJ	Conforms
Weight (reference value)	0.011 g

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